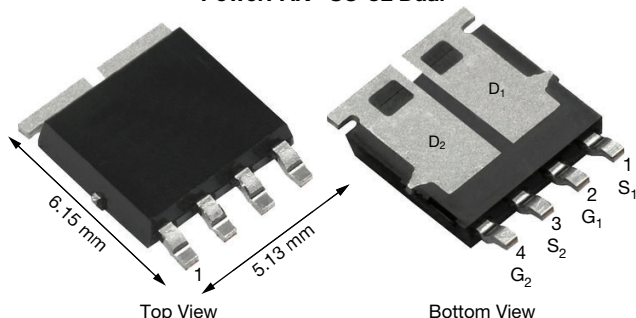


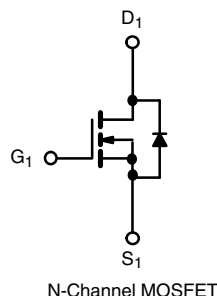
Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L Dual


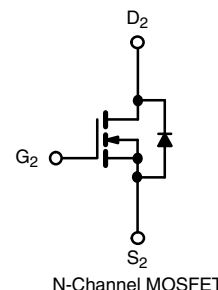
FEATURES

- TrenchFET® Gen IV Power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET



N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.008
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.010
I_D (A) per leg	30
Configuration	Dual

ORDERING INFORMATION

Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJB46ELP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	40	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	30	A
		27	
Continuous source current (diode conduction) ^a	I_S	30	
Pulsed drain current ^b	I_{DM}	120	
Single pulse avalanche current	I_{AS}	20.5	mJ
Single pulse avalanche energy	E_{AS}	21	
Maximum power dissipation	P_D	34	W
		11	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^d		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	85	°C/W
Junction-to-case (drain)	R_{thJC}	4.3	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leaded package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

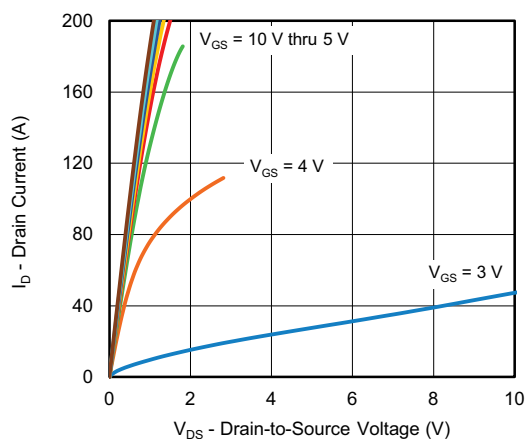
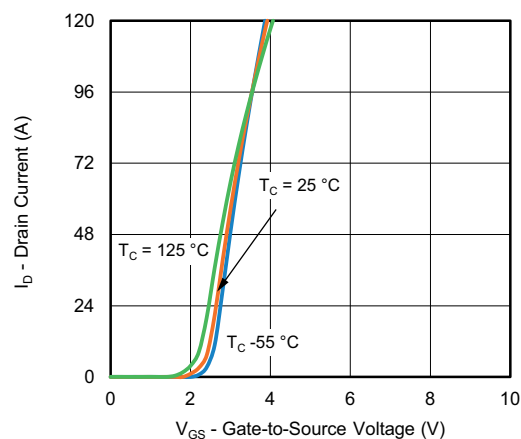
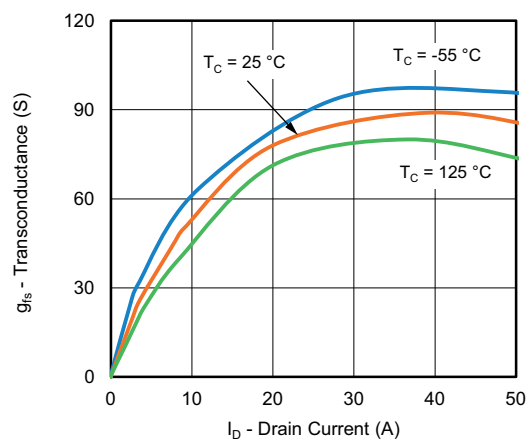
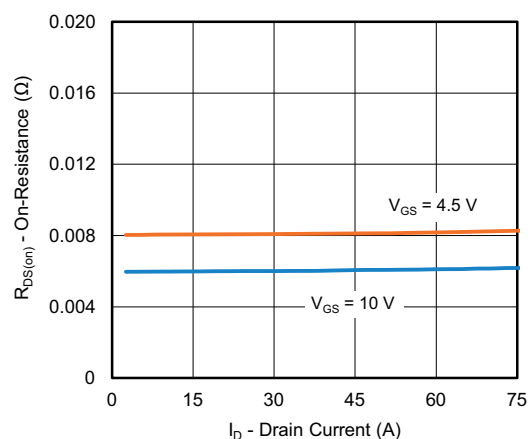
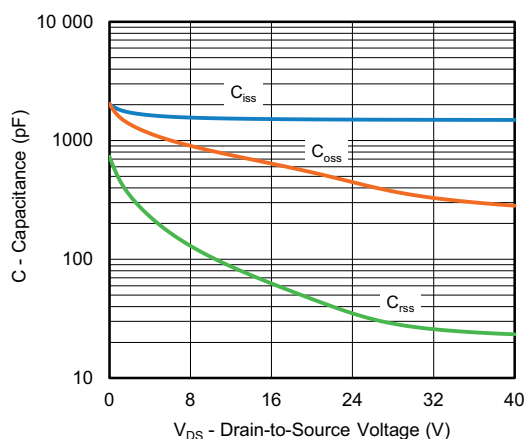
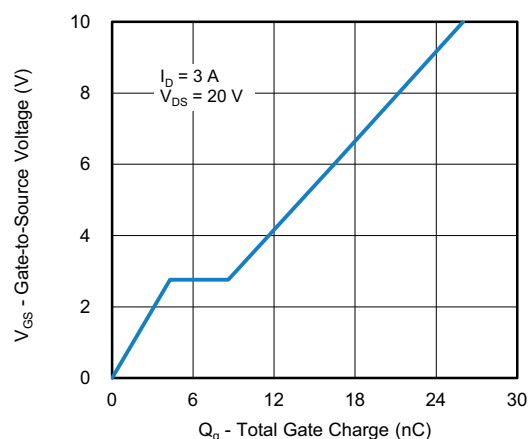


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.2	1.7	2.2	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	25	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 8 A	-	0.0064	0.0080	Ω
		V _{GS} = 10 V	I _D = 8 A, T _J = 125 °C	-	-	0.0131	
		V _{GS} = 10 V	I _D = 8 A, T _J = 175 °C	-	-	0.0157	
		V _{GS} = 4.5 V	I _D = 5 A	-	0.0080	0.0100	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 8 A		-	46	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	1499	2100	pF
Output capacitance	C _{oss}			-	426	600	
Reverse transfer capacitance	C _{rss}			-	34	48	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 3 A	-	26	40	nC
Gate-source charge ^c	Q _{gs}			-	4.3	-	
Gate-drain charge ^c	Q _{gd}			-	4.3	-	
Gate resistance	R _g	f = 1 MHz		1.26	2.54	3.8	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 6.67 Ω I _D ≅ 3 A, V _{GEN} = 10 V, R _g = 1 Ω		-	10	20	ns
Rise time ^c	t _r			-	5	10	
Turn-off delay time ^c	t _{d(off)}			-	25	40	
Fall time ^c	t _f			-	6	12	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	120	A
Forward voltage	V _{SD}	I _F = 8 A, V _{GS} = 0 V		-	0.79	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 6 A, di/dt = 100 A/μs		-	26	55	ns
Body diode reverse recovery charge	Q _{rr}			-	15	33	nC
Reverse recovery fall time	t _a			-	13	-	ns
Reverse recovery rise time	t _b			-	13	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.97	-	A

Notes

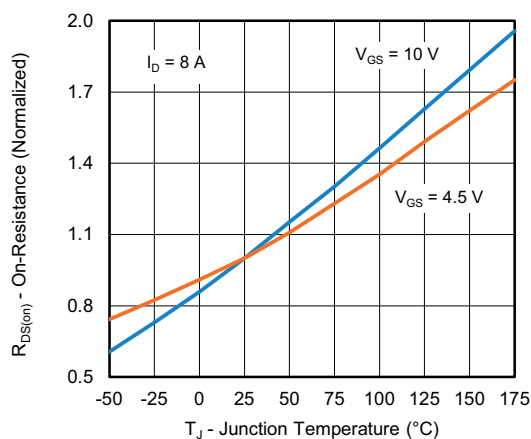
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

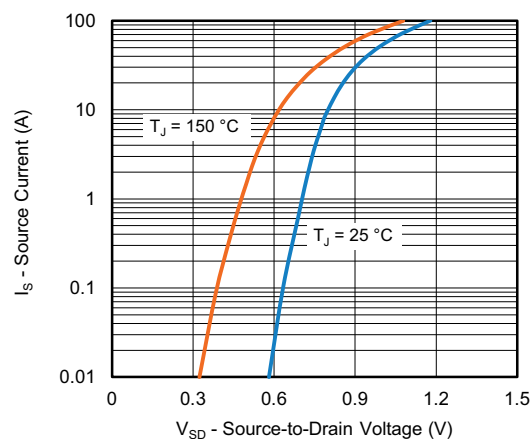
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge



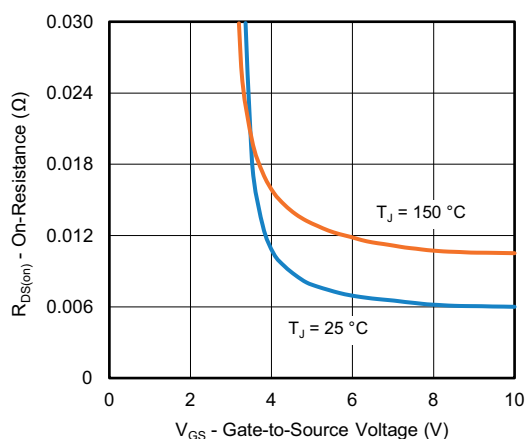
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



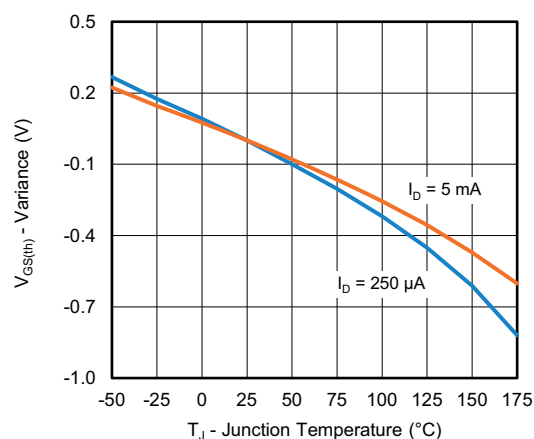
On-Resistance vs. Junction Temperature



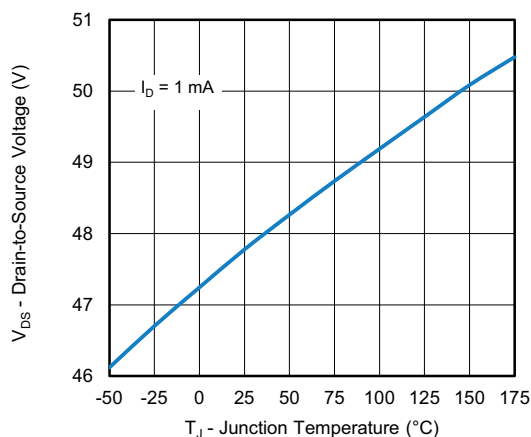
Source Drain Diode Forward Voltage



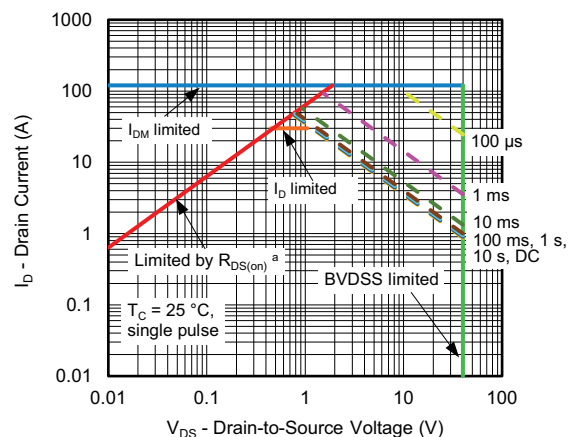
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



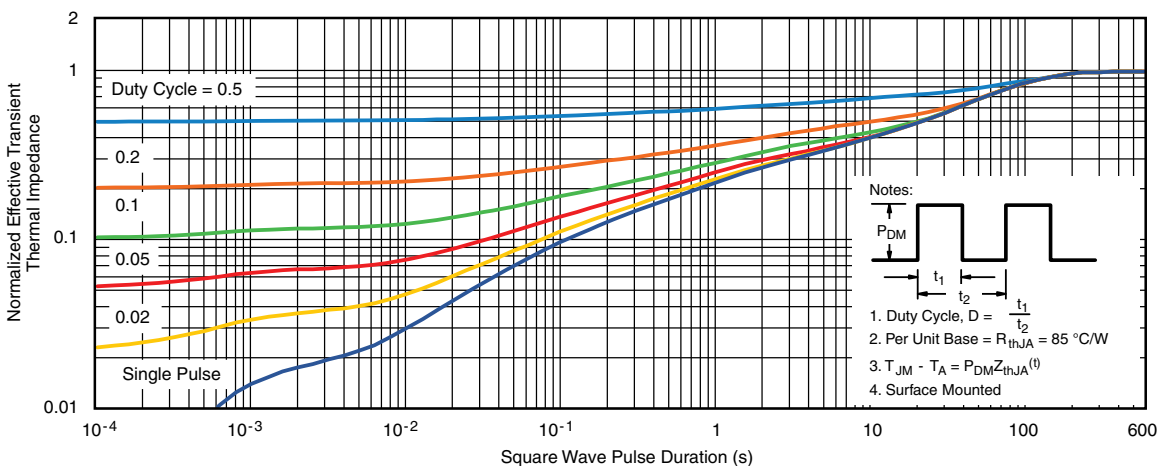
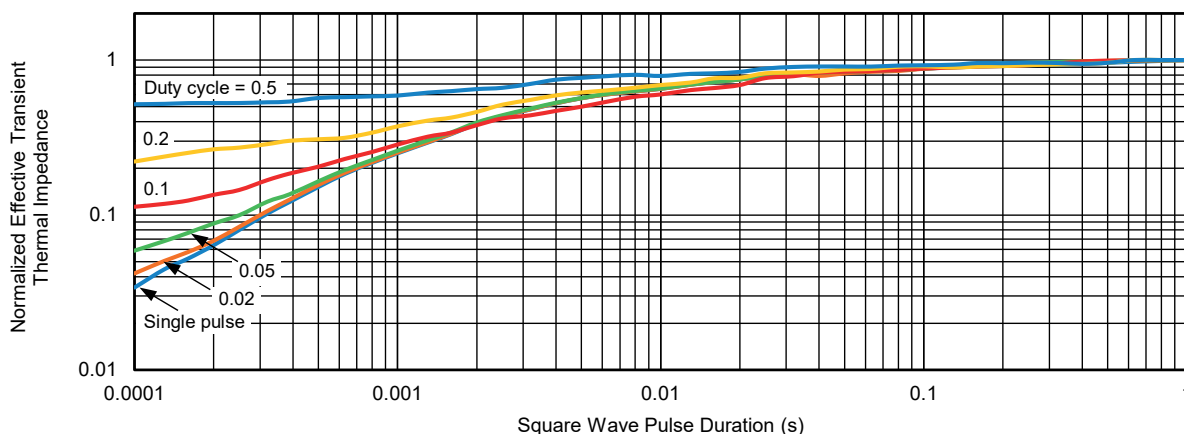
Drain Source Breakdown vs. Junction Temperature



Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

**THERMAL RATINGS** ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case****Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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